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EE C247B - ME C218 Introduction to MEMS Design Spring 2017

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Lecture Module 14: Sensing Circuits

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Lecture Outline

- Reading: Senturia, Chpt. 14
- Lecture Topics:
 - ↳ Detection Circuits
 - ↳ Velocity Sensing
 - ↳ Position Sensing

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Position-to-Voltage Conversion

• To sense position (i.e., displacement), use a capacitive load

Again, have port-to-port I/O symmetry:

Brute force approach:

$$\frac{N_o}{V_i}(s) = \frac{1}{R_x + \frac{1}{sC_x} + sL_x + \frac{1}{sC_D}}$$

$$\frac{N_o}{V_i}(s) = \frac{C_x/C_D}{sR_xC_x + 1 + s^2L_xC_x + \frac{sC_x}{1+C_x/C_D}} = \frac{C_x/C_D}{1 + \frac{sR_xC_x}{1+C_x/C_D} + s^2 \frac{L_xC_x}{1+C_x/C_D}}$$

Gain Term DC Gain Lat-Pole BiQuad

To maximize gain $\rightarrow 1$, need $C_D \ll C_x$. (must minimize C_D)

Note: Can we similar short-cut to the R case.

- ① Get DC response $\rightarrow C$'s dominate.
- ② Then.

$$\frac{N_o}{V_i}(s) = (\text{DC Gain}) \cdot \frac{1}{s} \cdot \Theta(s, \omega_0, Q) \cdot \omega_0^2 Q$$

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Voltage Representing Position

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Position Sensing Circuits

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Problems With Pure-C Position Sensing

- To sense position (i.e., displacement), use a capacitive load

$$\frac{V_o}{V_i}(s) = \frac{Cx/C_b}{1 + Cx/C_D} \cdot \frac{1}{s} \cdot \Theta(s, \omega_0, Q) \cdot \omega_0^2$$

Integration yields displacement.
To maximize gain, minimize C_b .
⇒ Problem: parasitic capacitance
 $C_b \rightarrow C_b + C_{p_i} + C_{p_b}$
⇒ DC Gain: $\frac{Cx / (Cx + C_{p_i} + C_{p_b})}{1 + Cx / (C_0 + C_{p_i} + C_{p_b})}$
Output will get smaller!
Remedy: Suppress C_p via use of op amps.

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The Op Amp Integrator Advantage

- The virtual ground provided by the ideal op amp eliminates the parasitic capacitance C_p

$R_2 \gg \frac{1}{sC_2}$ (for biasing)
 $R_0 = 0 \Omega$
Can drive next stages
 R_i w/o interference to transfer function!

well defined → good!
 $N_o = -i_o (R_2 // \frac{1}{sC_2})$
 $\approx -\frac{N_i}{R_x} \Theta(s) \frac{1}{sC_2} \Rightarrow \frac{N_o}{N_i}(s) = -\frac{1}{R_x C_2} \frac{\Theta(s)}{s}$

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